

#### November 2015

## FDPF190N15A N-Channel PowerTrench<sup>®</sup> MOSFET 150 V, 27.4 A, 19 mΩ

### Features

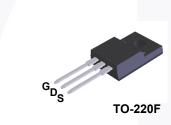
- $R_{DS(on)}$  = 14.7 m $\Omega$  (Typ.) @ V<sub>GS</sub> = 10 V, I<sub>D</sub> = 27.4 A
- Low Gate Charge, Q<sub>G</sub> = 31 nC (Typ.)
- Low C<sub>rss</sub> (Typ. 56 pF)
- · Fast Switching Speed
- · Improved dv/dt Capability
- RoHS Compliant

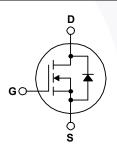
### Description

This N-Channel MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench<sup>®</sup> process that has been tailored to minimize the on-state resistance while maintaining superior switching performance.

### Applications

- Consumer Appliances
- LED TV
- · Synchronous Rectification for ATX / Sever / Telecom PSU
- Uninterruptible Power Supply
- Micro Solar Inverter





#### Absolute Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted.

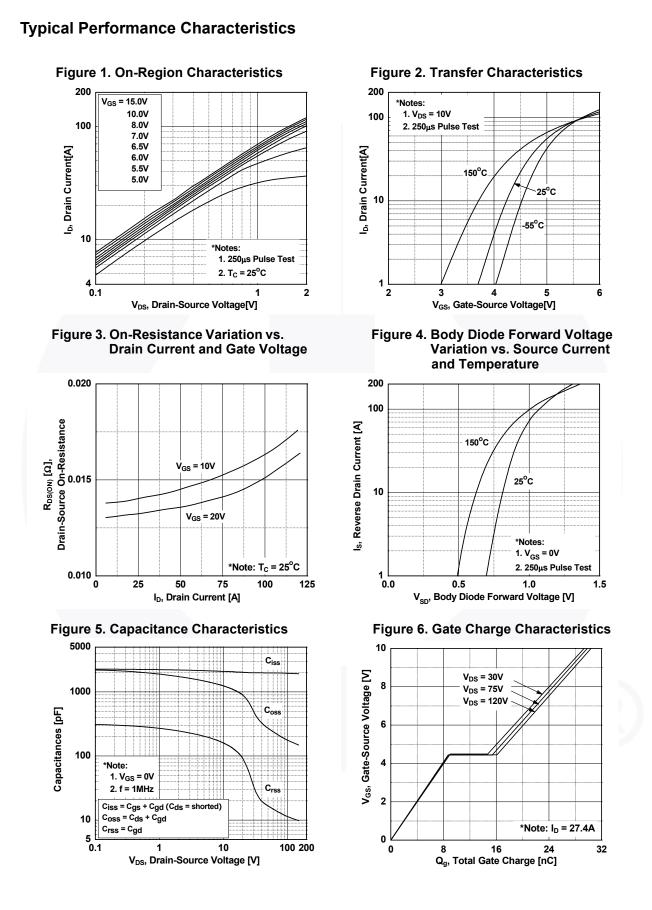
Symbol		FDPF190N15A	Unit			
V <sub>DSS</sub>	Drain to Source Voltage		150	V		
V <sub>GSS</sub>	Cata ta Sauraa Valtaga	- DC	±20	V		
	Gate to Source Voltage	- AC	(f > 1 Hz)	±30	V	
ID	Drain Current	- Continuous (T <sub>C</sub> = 25 <sup>o</sup> C)		27.4	— A	
	Drain Current	- Continuous (T <sub>C</sub> = 100 <sup>o</sup> C)		17.4		
I <sub>DM</sub>	Drain Current	- Pulsed	(Note 1)	110	Α	
E <sub>AS</sub>	Single Pulsed Avalanche Energy (Note 2			261	mJ	
dv/dt	Peak Diode Recovery dv/dt (Note 3)		(Note 3)	6.0	V/ns	
P <sub>D</sub>	Dower Dissinction	(T <sub>C</sub> = 25 <sup>o</sup> C)		33	W	
	Power Dissipation	- Derate Above 25°C		0.26	W/ºC	
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range			-55 to +150	°C	
TL	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds			300	°C	

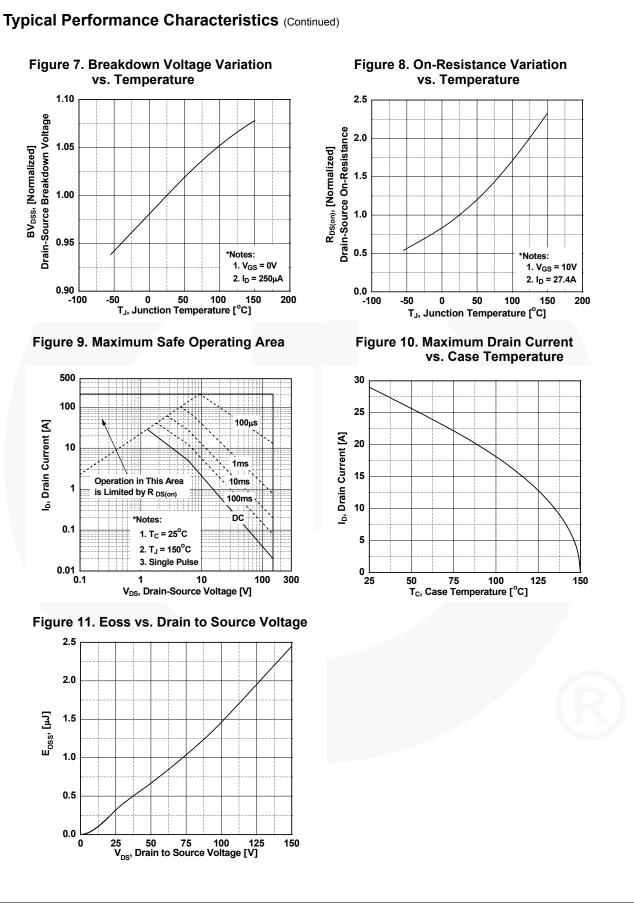
### **Thermal Characteristics**

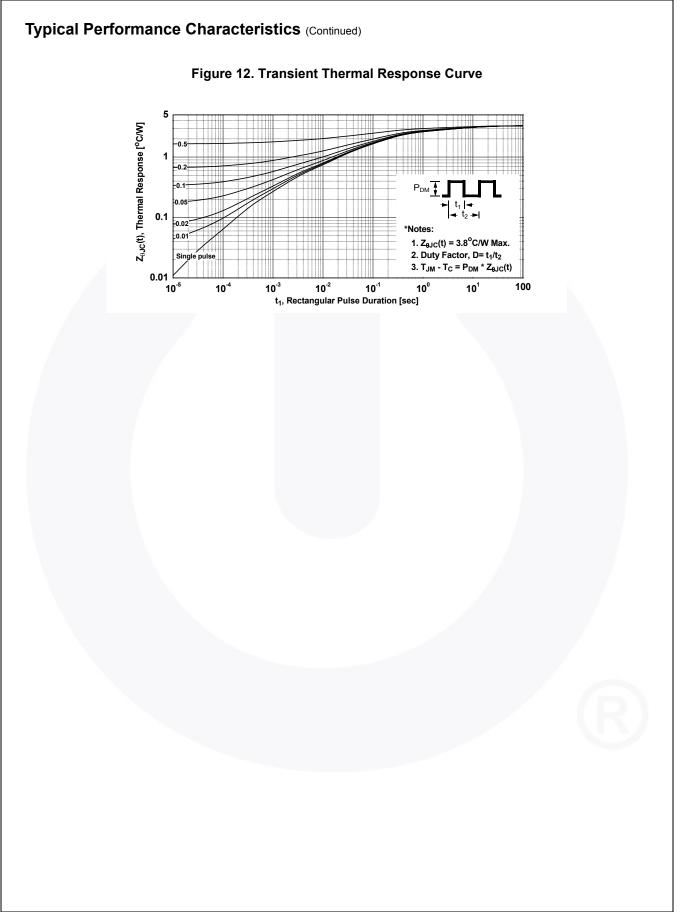
Symbol	Parameter	FDPF190N15A	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	3.3	°C/W
$R_{ hetaJA}$	Thermal Resistance, Junction to Ambient, Max.	62.5	°C/W

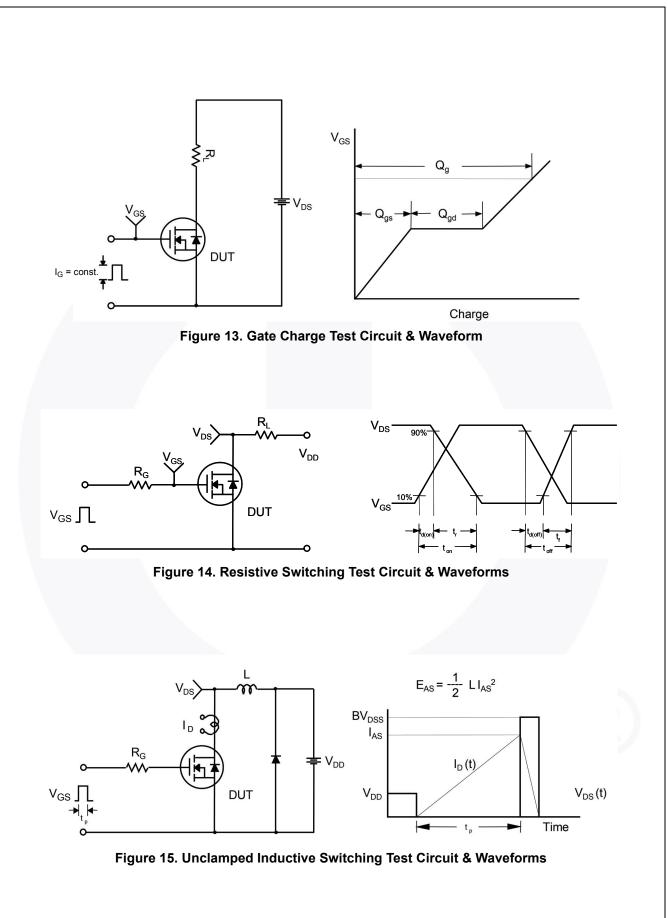
Part Nu	Part Number Top Mark Pag		Package	Packing Method	Reel Size	e	Tape Width	ı Qu	Quantity	
		TO-220F	0F Tube N/A		N/A		50 units			
Electrica	I Chara	acteristics T <sub>c</sub> = 25 <sup>c</sup>	<sup>o</sup> C unless of	therwise noted.						
Symbol				Test Conditio	ons	Min.	Тур.	Max.	Unit	
Off Charac	teristics	6								
BV <sub>DSS</sub>	Drain to	Source Breakdown Voltag	ae	I <sub>D</sub> = 250 μA, V <sub>GS</sub> = 0 V		150	-	-	V	
$\Delta BV_{DSS}$		wn Voltage Temperature	-							
$/\Delta T_J$		oefficient $I_D = 250 \ \mu$ A, Referenced to $25^{\circ}$ C		d to 25°C	-	0.14	-	V/ºC		
	Zero Gate Volta		$V_{DS} = 120 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$			-	-	1	μA	
I <sub>DSS</sub> Zero G				$V_{DS} = 120 \text{ V}, \text{ T}_{C} = 150^{\circ}\text{C}$		-	-	500	μι	
I <sub>GSS</sub>	Gate to Body Leakage Current		Y	$V_{GS}$ = ±20 V, $V_{DS}$ = 0 V		-	-	±100	nA	
On Charac	teristics									
V <sub>GS(th)</sub>	Gate Thr	reshold Voltage	,	V <sub>GS</sub> = V <sub>DS</sub> , I <sub>D</sub> = 250 μA		2.0	-	4.0	V	
R <sub>DS(on)</sub>	Static Dr.	ain to Source On Resista		V <sub>GS</sub> = 10 V, I <sub>D</sub> = 27.4 A		-	14.7	19.0	mΩ	
9 <sub>FS</sub>	Forward	Transconductance		V <sub>DS</sub> = 10 V, I <sub>D</sub> = 27.4 A		-	64	-	S	
Dynamic C	-								1	
C <sub>iss</sub>		pacitance		V <sub>DS</sub> = 25 V, V <sub>GS</sub> = 0 V, f = 1 MHz		-	2020	2685	pF	
C <sub>oss</sub>		apacitance				-	700	930	pF	
C <sub>rss</sub>		Transfer Capacitance				-	56	85	pF	
C <sub>oss(er)</sub>		Related Output Capacitan	ce	V <sub>DS</sub> = 75 V, V <sub>GS</sub> = 0 V		-	252	-	pF	
Q <sub>g(tot)</sub>		e Charge at 10V	,	V <sub>DS</sub> = 120 V, I <sub>D</sub> = 27.4	А,	-	30	39	nC	
Q <sub>gs</sub>		Source Gate Charge	'	V <sub>GS</sub> = 10 V		-	8.8	-	nC	
Q <sub>gd</sub>		Drain "Miller" Charge			(Note 4)	-	7.3	-	nC	
ESR	Equivale	nt Series Resistance (G-	S) ·	f = 1 MHz		-	1.5	-	Ω	
	Charact	eristics								
Switching	Turn-On	Delay Time				-	18	46	ns	
	Turn-On	Rise Time		V <sub>DD</sub> = 75 V, I <sub>D</sub> = 27.4 A		-	16	42	ns	
t <sub>d(on)</sub>				$V_{GS}$ = 10 V, R <sub>G</sub> = 4.7 Ω (Note 4)			32	74	ns	
t <sub>d(on)</sub> t <sub>r</sub>	Turn-Off	Delay Time					8	26	ns	
Switching           t <sub>d(on)</sub> t <sub>r</sub> t <sub>d(off)</sub> t <sub>f</sub>		Delay Time Fall Time			(Note 4)					
t <sub>d(on)</sub> t <sub>r</sub> t <sub>d(off)</sub> t <sub>f</sub>	Turn-Off	Fall Time			(Note 4)	7	<b>I</b>			
t <sub>d(on)</sub> t <sub>r</sub> t <sub>d(off)</sub> t <sub>f</sub> Drain-Sou	Turn-Off	Fall Time e Characteristics		Forward Current	(Note 4)	<u> </u>	-	27.4	A	
t <sub>d(on)</sub> t <sub>r</sub> t <sub>d(off)</sub> t <sub>f</sub> Drain-Sou	Turn-Off rce Diod	Fall Time	urce Diode		(Note 4)	/	-	27.4 110	A	
t <sub>d(on)</sub> t <sub>r</sub> t <sub>d(off)</sub> t <sub>f</sub> <b>Drain-Sou</b> I <sub>S</sub> I <sub>SM</sub>	Turn-Off rce Diod Maximum Maximum	Fall Time e Characteristics n Continuous Drain to So	urce Diode Diode Forw	ard Current	(Note 4)	/			-	
t <sub>d(on)</sub> t <sub>r</sub> t <sub>d(off)</sub> t <sub>f</sub> Drain-Sou	Turn-Off rce Diod Maximum Maximum Drain to S	Fall Time e Characteristics n Continuous Drain to Sou n Pulsed Drain to Source	urce Diode Diode Forw Ditage			/	- - - 76	110	Α	

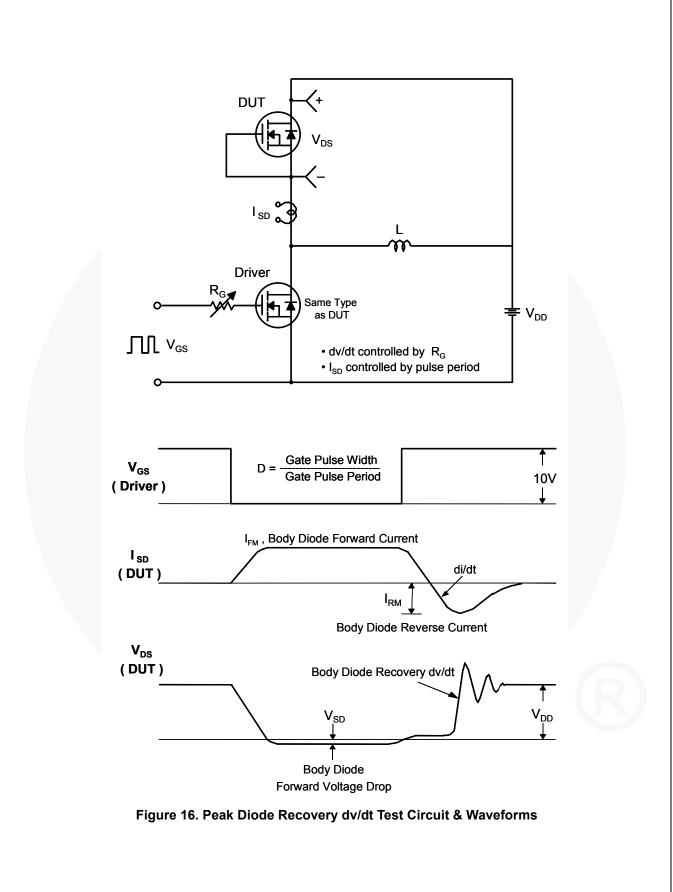
1. Repetitive rating: pulse-width limited by maximum junction temperature. 2. L = 0.33 mH, I<sub>AS</sub> = 29 A, R<sub>G</sub> = 25  $\Omega$ , starting T<sub>J</sub> = 25°C. 3. I<sub>SD</sub>  $\leq$  27.4 A, di/dt  $\leq$  200 A/µs, V<sub>DD</sub>  $\leq$  BV<sub>DSS</sub>, starting T<sub>J</sub> = 25°C. 4. Essentially independent of operating temperature typical characteristics.

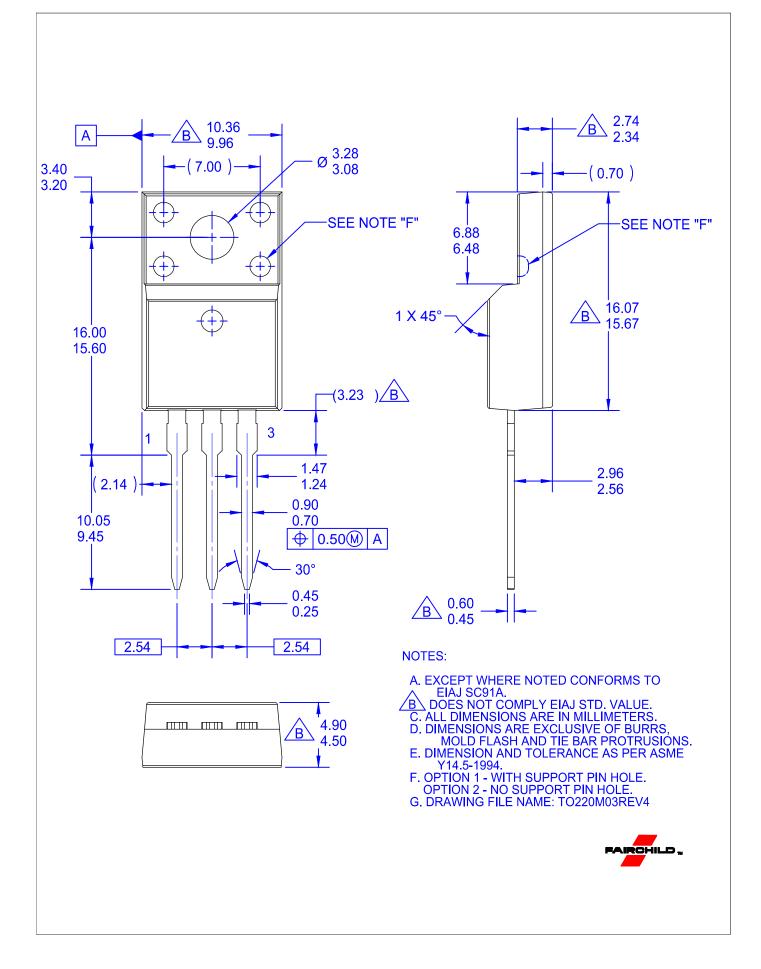














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